

EECS 42 Intro. Digital Electronics, Fall 2003 Lecture 17: 10/23/03 A.R. Neureuther
Version Date 10/18/03

EECS 42 Introduction Digital Electronics

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These viewgraphs will be handed out in class.

Lecture # 17 Logic with Complementary Devices
S&O pp. 607-611 (read for graphs and not physics or equations), plus Handout of Wed Lectures.

- A) Discovering a Pull-Up Device
- B) Designing a Pull-Up Device
- C) EE 42 Pull-Up Device Model (42S_P MOS)
- D) Composite I_{OUT} vs. V_{OUT}
- E) Voltage Transfer Function and V_{MID}

<http://inst.EECS.Berkeley.EDU/~ee42/>

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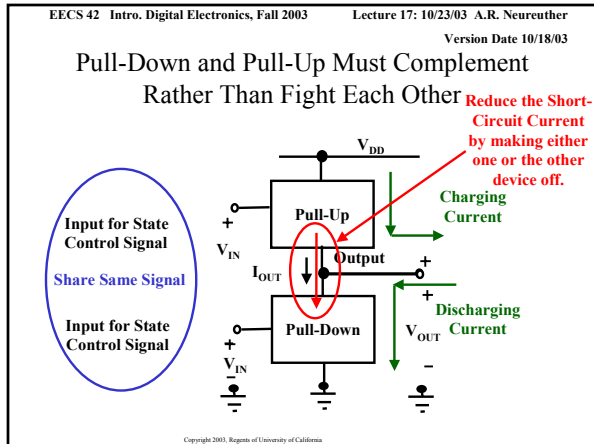
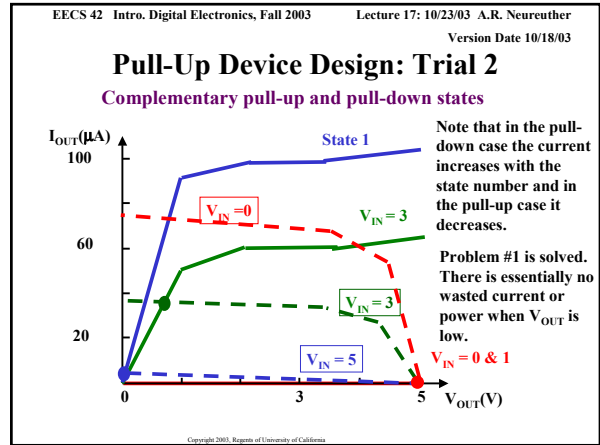
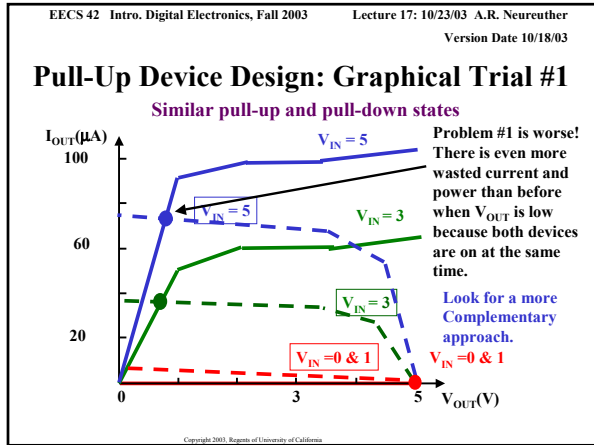
Problems and Opportunities in Logic Circuit Design

Problem #1: Significant wasted current and power when V_{OUT} is low.
Problem #2: High value of V_{OUT} is adversely affected by a load resistor.

Missed Opportunity: The value of the input control signal is not used to adjust the state of the pull-up device.

What if : If the pull-up device could be a state-dependent device what kind of device would we want?

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Desirable Complementary Device Characteristics

	V_{IN}	Low	High
Pull-Down Current		Low not leak	High Discharge Output
Pull-Up Current		High Charge Output	Low not leak

We desire characteristics that are **complementary** for the pull-down and pull-up state-dependent devices.

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Designing the Complementary Device

Make This

Into This

The curve sets are very similar but have two key changes.
 The creation of current with input State (V_{IN}) is reverse ordered (and also shifted).
 The dependence on V_{OUT} is reversed in sign and shifted by V_{DD}

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Pull-Up Can be viewed as Complementary by using Device rather than Circuit voltages $V_{DD}-V_X$

$V'_{IN} = V_{DD} - V_{IN}$
 $V'_{OUT} = V_{DD} - V_{OUT}$
 Shift Reverse

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Saturation Current NMOS Model

Current I_{OUT} only flows when V_{IN} is larger than the threshold value V_{TD} and the current is proportional to V_{OUT} up to $V_{OUT-SAT-D}$ where it reaches the saturation current

$$I_{OUT-SAT-D} = k_D (V_{IN} - V_{TD}) V_{OUT-SAT-D}$$

Note that we have added an extra parameter to distinguish between threshold (V_{TD}) and saturation ($V_{OUT-SAT-D}$).

Example:
 $k_D = 25 \mu A/V^2$ Use these values in the homework.
 $V_{TD} = 1V$
 $V_{OUT-SAT-D} = 1V$

$I_{OUT-SAT-D} = 25 \frac{\mu A}{V^2} (3V - 1V) 1V = 50 \mu A$

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Saturation Current 42S_P MOS Model

Current I_{OUT} only flows when V_{IN} is smaller than V_{DD} by the threshold value V_{TU} (that is $V_{DD} - V_{IN} > V_{TU}$) and the current is proportional to the excess gate voltage ($V_{DD} - V_{IN} - V_{TU}$) and is also proportional to ($V_{DD} - V_{OUT}$) above ($V_{DD} - V_{OUT-SAT-U}$) where it has its maximum saturated value.

$$I_{OUT-SAT-U} = k_U (V_{DD} - V_{IN} - V_{TU}) V_{OUT-SAT-U}$$

Example: Use these values in the homework.
 $k_U = 20 \mu A/V^2$
 $V_{TU} = 1V$
 $V_{OUT-SAT-U} = 1V$

$I_{OUT-SAT-U} = 20 \frac{\mu A}{V^2} (5V - 3V - 1V) 1V = 20 \mu A$

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42S_P MOS Pull-UP Device Curves

I_{OUT} vs. V_{OUT}

Evaluating the current when $V_{OUT} = V_{DD} - V_{OUT-SAT-U}$ for a given V_{IN} allows the entire curve to be sketched

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Transistor Inverter Example

It may be simpler to just think of PMOS and NMOS transistors instead of a general 3 terminal pull-up or pull-down devices or networks.

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